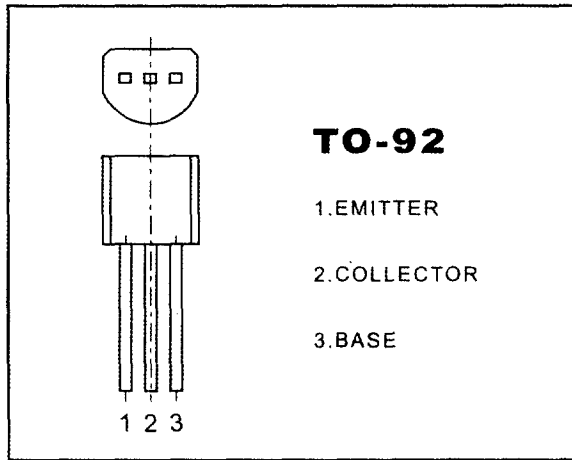


TO-92 Plastic-Encapsulate Transistors

2SC1213 / 2SC1213A TRANSISTOR(NPN)



FEATURES

Power dissipation

P_{CM} : 0.4W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : 0.5 A

Collector-base voltage

$V_{(BR)CBO}$: 2SC1213 : 35V

2SC1213A : 50V

Operating and storage junction temperature range

$T_{j, T_{sig}}$: $-55^{\circ}C$ to $+150^{\circ}C$

ELECTRICAL CHARACTERISTICS

($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	2SC1213	2SC1213A	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_c = 10 \mu A, I_E = 0$	35	50	V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_c = 1 mA, I_b = 0$	35	50	V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 10 \mu A, I_c = 0$	4		V
Collector cut-off current	I_{cbo}	$V_{cb} = 20 V, I_E = 0$		0.5	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = 3 V, I_c = 10 mA$	60	320	
	$h_{FE(2)}$	$V_{CE} = 3 V, I_c = 500 mA$	10		
Collector-emitter saturation voltage	V_{CEsat}	$I_c = 150 mA, I_b = 15 mA$		0.6	V
Base-emitter voltage	V_{BE}	$V_{CE} = 3 V, I_c = 10 mA$		0.64	V

CLASSIFICATION OF $h_{FE(1)}$

Rank	B	C	D
Range	60-120	100-200	160-320

Typical Characteristics

2SC1213 2SC1213A

